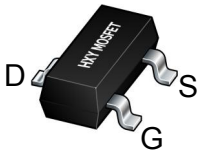
General Description

The ST1002 use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness and suitable to use in

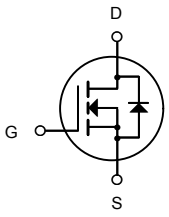


SOT-23-3L

General Features

V_{DS} =100V I_D =5 A

$R_{DS(ON)}$ < 140mΩ@ V_{GS}=10V



N-Channel MOSFET

Applications

Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
ST1002	SOT-23-3L	HXY MOSFET	3000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V	5	A
I_D@T_C=70℃	Continuous Drain Current, V_{GS} @ 10V	2.2	A
I_{DM}	Pulsed Drain Current[2]	11	A
P_D@T_C=25℃	Total Power Dissipation[4]	1	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JC}$	Thermal Resistance from Junction-to-Ambient[3]	80	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	125	℃/W

Electrical Characteristics T_C=25℃ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	100	110	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 100V, V_{GS} = 0V	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics note3						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.95	3.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance note2	V_{GS} = 10V, I_D = 3A	-	95	140	mΩ
Dynamic Characteristics note4						
C_{iss}	Input Capacitance	V_{DS} = 50V, V_{GS} = 0V, f = 1.0MHz	-	196	-	pF
C_{oss}	Output Capacitance		-	25.9	-	pF
C_{rss}	Reverse Transfer Capacitance		-	21.4	-	pF
Q_g	Total Gate Charge	V_{DS} = 50V, I_D = 3A, V_{GS} = 10V	-	4.3	-	nC
Q_{gs}	Gate-Source Charge		-	3.5	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	3.1	-	nC
Switching Characteristics note4						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50V, I_{DS}=3A R_G = 2Ω, V_{GEN} = 10V	-	14.7	-	ns
t_r	Turn-On Rise Time		-	3.5	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	20.9	-	ns
t_f	Turn-Off Fall Time		-	2.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current note2		-	-	4.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V_{SD}	Drain to Source Diode Forward Voltage note3	V_{GS} = 0V, I_S =3A	-	-	1.3	V
t_{rr}	Body Diode Reverse Recovery Time	V_{GS} = 0V, I_F = 3A, di/dt =100A/μs	-	32.1	-	ns
Q_{rr}	Body Diode Reverse Recovery Time Charge		-	39.4	-	nC
I_{rrm}	Peak Reverse Recovery Current		-	2.1	-	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤2%.
4. Guaranteed by design, not subject to production
5. V_{DD}=50 V, R_G=50 Ω, L=0.3 mH, starting T_j=25 °C

Typical Characteristics

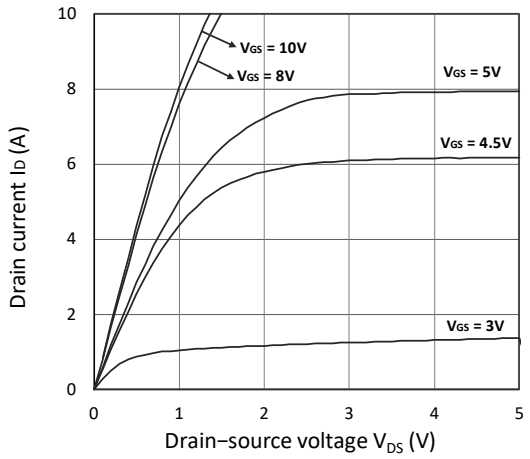


Figure 1. Output Characteristics

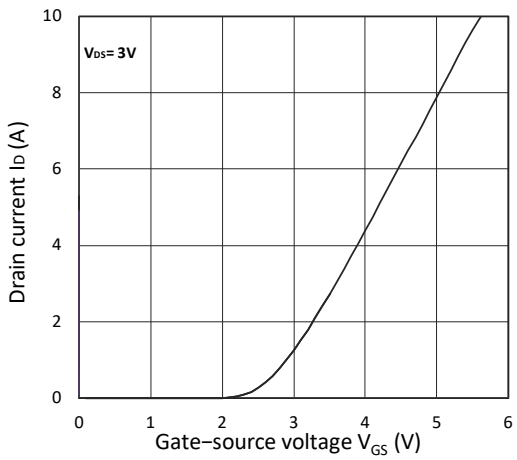


Figure 2. Transfer Characteristics

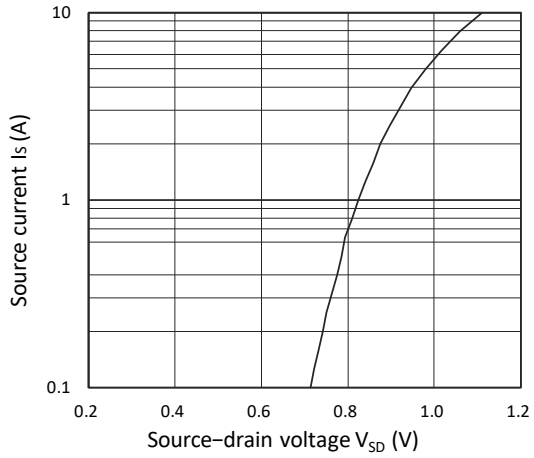


Figure 3. Forward Characteristics of Reverse

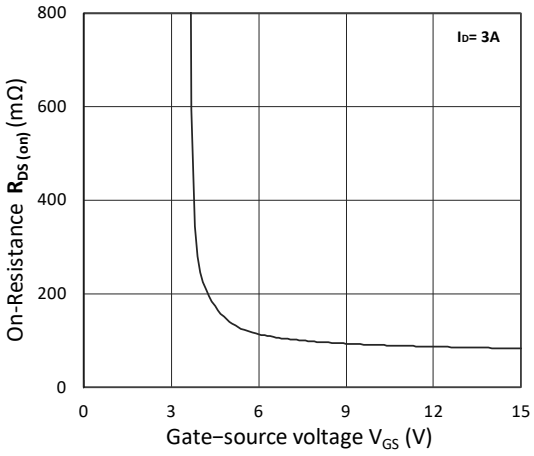


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

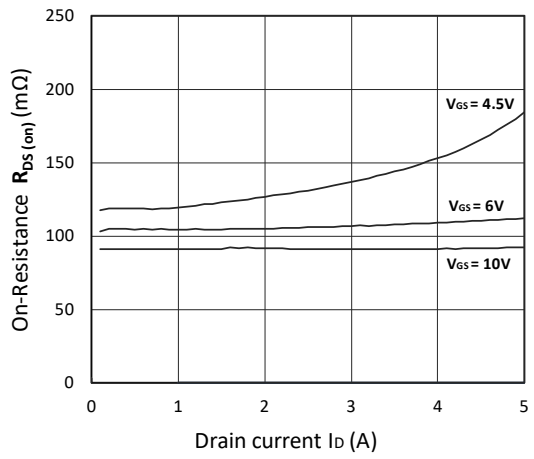


Figure 5. $R_{DS(ON)}$ vs. I_D

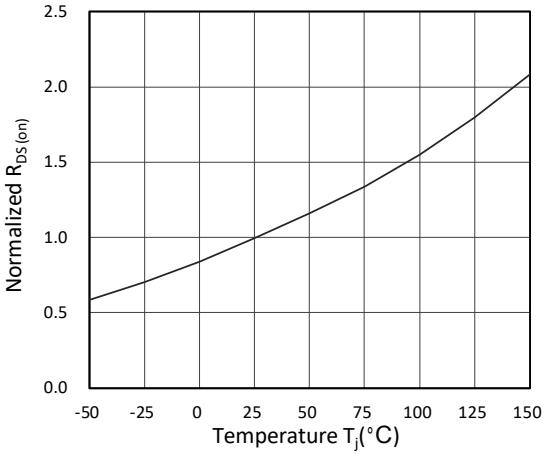


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

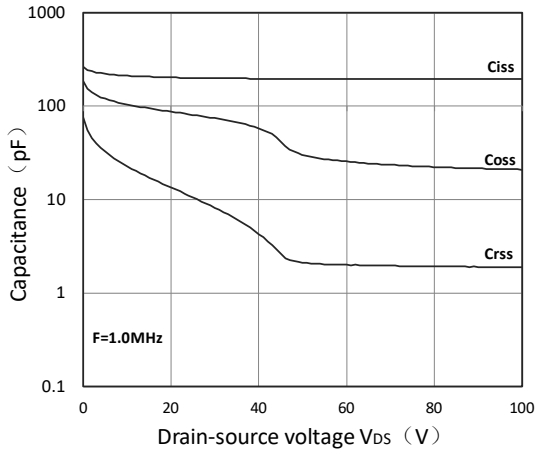


Figure 7. Capacitance Characteristics

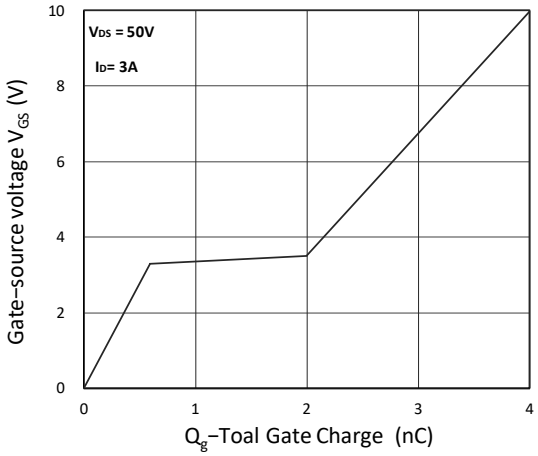
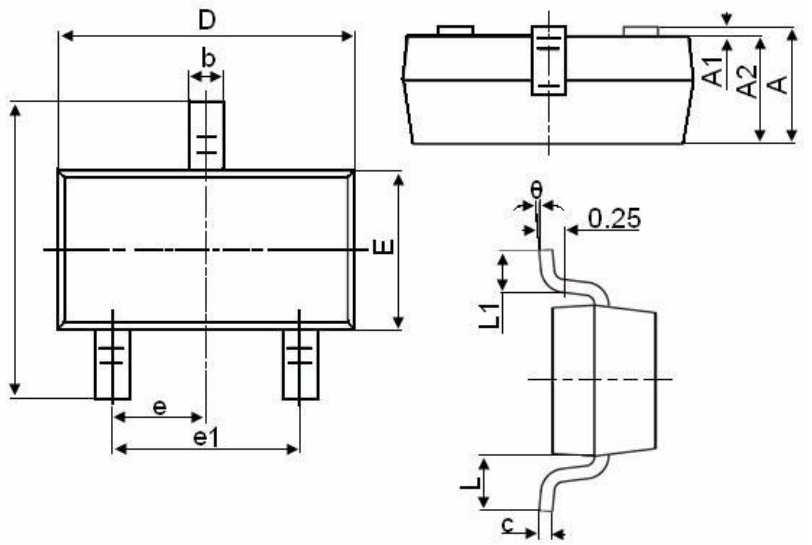


Figure 8. Gate Charge Characteristics

SOT-23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

Attention

■ Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.

■ HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.

■ Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could
give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by HXY MOS ***manufacturer:***

Other Similar products are found below :

IRFD120 JANTX2N5237 BUK455-60A/B MIC4420CM-TR VN1206L NDP4060 SI4482DY IPS70R2K0CEAKMA1 SQD23N06-31L-GE3 TK16J60W,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 DMN1053UCP4-7 SQJ469EP-T1-GE3 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B IPB80P04P405ATMA2 2N7002W-G MCAC30N06Y-TP MCQ7328-TP BXP7N65D BXP4N65F AOL1454G WMJ80N60C4 BXP2N20L BXP2N65D BXT1150N10J BXT1700P06M TSM60NB380CP ROG RQ7L055BGTCR DMNH15H110SK3-13 SLF10N65ABV2 BSO203SP BSO211P IPA60R230P6 IPA60R460CE